Features

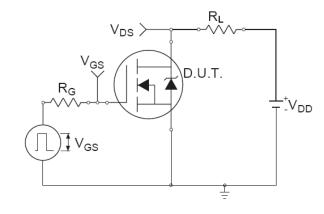
- V_{DSS} =80V/ V_{GSS} =±25V/ I_{D} =150A $R_{DS(ON)}$ =5m Ω (max.)@ V_{GS} =10V
- Low Dense Cell Design
- Reliable and Rugged
- Advanced trench process technology

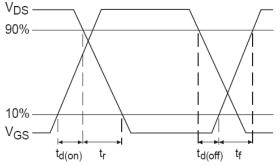
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Applications

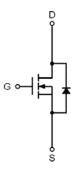
- Synchronous Rectification
- Power Management in Inverter System

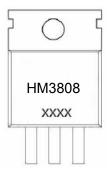
Switching Time Test Circuit and Waveforms





Pin Description





Marking and pin Assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity	
HM3808	HM3808	TO-220-3L	-	-	-	

Electrical Characteristics of CP Test (TA=25°C unless otherwise noted)

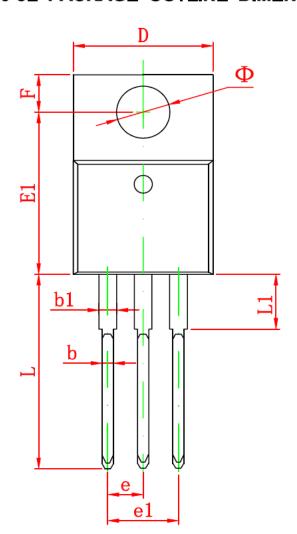
Symbol	Parameter	Test Conditions		Min.	Тур	Max.	Unit
Static Char	racteristics		-				
$\mathrm{BV}_{\mathrm{DSS}}$	Drain-Source Breakdown Voltage	V _{GS} =0V,I _D =250uA		80			V
Ţ	Zero Gate Voltage Drain Current	$V_{DS}=64V, V_{GS}=0V$				1	uA
I_{DSS}		Γ	T _J =85°C			30	
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250uA V _{GS} =±25V, V _{DS} =0V V _{GS} =10V, I _D =30A		2	2.6	4	V
I_{GSS}	Gate Leakage Current					±100	nA
R _{DS(on)}	Drain-Source On-Resistance				3.6	5	mΩ
V_{SD}	Diode Forward Voltage	I_{SD} =30A, V_{GS} =0V	V			1.3	V
R_{G}	Gate Resistance	V _{GS} =0V, V _{DS} =0V, Frequency=1MHz			1.7		Ω

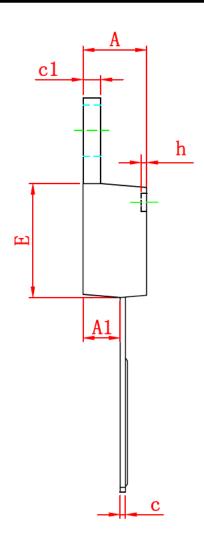
Note: 1: Pulse test; pulse width ≤ 300 ns, duty cycle $\leq 2\%$.

^{2:} Guaranteed by design, not subject to production testing.

 $: 2X_{\rm FU} / \tilde{\rm O}47X_{\rm I~U} / 372C * K_F + 'P/E j~cppg n'Gp j~c~pego~gpv'O~qf~g'O~QUHGV''$

TO-220-3L PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions	In Millimeters	Dimensions In Inches			
Syllibol	Min	Max	Min	Max		
Α	4.470	4.670	0.176	0.184		
A1	2.520	2.820	0.099	0.111		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.310	0.530	0.012	0.021		
c1	1.170	1.370	0.046	0.054		
D	10.010	10.310	0.394	0.406		
Е	8.500	8.900	0.335	0.350		
E1	12.060	12.460	0.475	0.491		
е	2.540) TYP	0.100 TYP			
e1	4.980	5.180	0.196	0.204		
F	2.590	2.890	0.102	0.114		
h	0.000	0.300	0.000	0.012		
L	13.400	13.800	0.528	0.543		
L1	3.560	3.960	0.140	0.156		
Ф	3.735	3.935	0.147	0.155		

''''**'''''J O 5: 2:** ''

: 2X_{FU}/O47X_{IU}/372C*K+''P/Ej cppgdGpj c pego gpv''O qf g'O QUHGV''

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